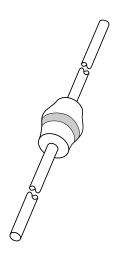
DISCRETE SEMICONDUCTORS

DATA SHEET



BYM99 Ultra fast low-loss controlled avalanche rectifier

Product specification
Supersedes data of June 1994
File under Discrete Semiconductors, SC01

1996 Feb 19





Ultra fast low-loss controlled avalanche rectifier

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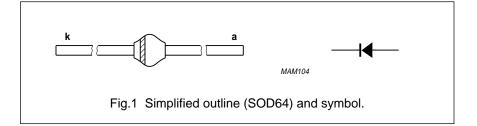
FEATURES

- Glass passivated
- Low leakage current
- · Excellent stability
- Guaranteed avalanche energy absorption capability
- Available in ammo-pack
- Also available with preformed leads for easy insertion.

DESCRIPTION

Rugged glass SOD64 package, using a high temperature alloyed construction.

This package is hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{RRM}	repetitive peak reverse voltage		_	600	V
V _R	continuous reverse voltage		_	600	V
I _{F(AV)}	average forward current	T _{tp} = 50 °C; lead length = 10 mm see Fig. 2; averaged over any 20 ms period; see also Fig 6	_	1.8	A
		T _{amb} = 60 °C; PCB mounting (see Fig.10); see Fig. 3; averaged over any 20 ms period; see also Fig. 6	_	0.8	A
I _{FRM}	repetitive peak forward current	T _{tp} = 50 °C; see Fig. 4	_	15	Α
		T _{amb} = 60 °C; see Fig. 5	_	7	Α
I _{FSM}	non-repetitive peak forward current	t = 10 ms half sine wave; $T_j = T_{j \text{ max}}$ prior to surge; $V_R = V_{RRMmax}$	_	40	A
E _{RSM}	non-repetitive peak reverse avalanche energy	L = 120 mH; $T_j = T_{j \text{ max}}$ prior to surge; inductive load switched off	_	10	mJ
T _{stg}	storage temperature		-65	+175	°C
Tj	junction temperature		-65	+150	°C

Philips Semiconductors Product specification

Ultra fast low-loss controlled avalanche rectifier

BYM99

ELECTRICAL CHARACTERISTICS

 $T_i = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	forward voltage	$I_F = 3 \text{ A}$; $T_j = T_{j \text{ max}}$; see Fig. 7	_	_	1.95	V
		I _F = 3 A; see Fig. 7	_	_	3.60	V
V _{(BR)R}	reverse avalanche breakdown voltage	I _R = 0.1 mA	700	_	_	V
I _R	reverse current	V _R = V _{RRMmax} ; see Fig. 8	_	_	5	μΑ
		$V_R = V_{RRMmax}$; $T_j = 150 ^{\circ}C$; see Fig. 8	_	_	75	μΑ
t _{rr}	reverse recovery time	when switched from $I_F = 0.5 \text{ A}$ to $I_R = 1 \text{ A}$; measured at $I_R = 0.25 \text{ A}$; see Fig. 12	_	_	15	ns
C _d	diode capacitance	$f = 1 \text{ MHz}$; $V_R = 0 \text{ V}$; see Fig. 9	_	135	_	pF
$\frac{\left dI_{R} \right }{dt}$	maximum slope of reverse recovery current	when switched from I_F = 1 A to $V_R \ge 30$ V and dI_F/dt = -1 A/ μ s; see Fig.11	_	_	3	A/μs

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point	lead length = 10 mm	25	K/W
R _{th j-a}	thermal resistance from junction to ambient	note 1	75	K/W

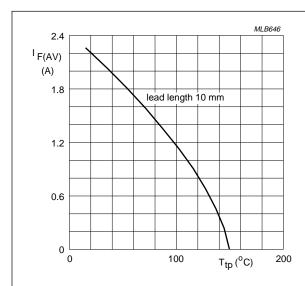
Note

1. Device mounted on an epoxy-glass printed-circuit board, 1.5 mm thick; thickness of Cu-layer ≥40 μm, see Fig.10. For more information please refer to the *'General Part of Handbook SC01'*.

Ultra fast low-loss controlled avalanche rectifier

BYM99

GRAPHICAL DATA



 $a = 1.42; \ V_R = V_{RRMmax}; \ \delta = 0.5.$ Switched mode application.

Fig.2 Maximum permissible average forward current as a function of tie-point temperature (including losses due to reverse leakage).

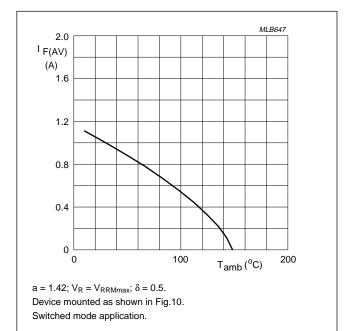
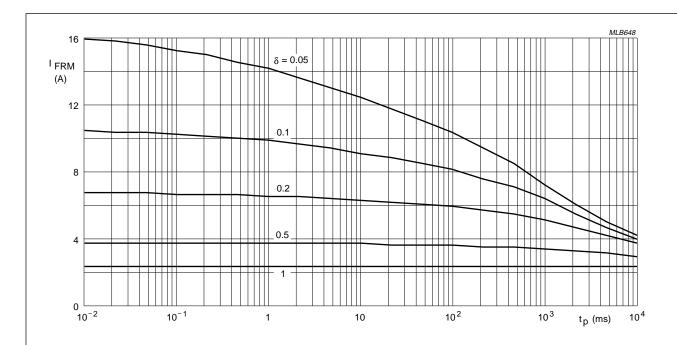


Fig.3 Maximum permissible average forward current as a function of ambient temperature (including losses due to reverse leakage).



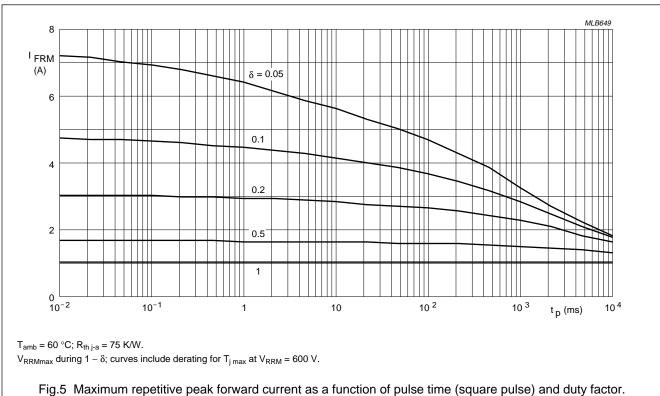
 T_{tp} = 50°C; $R_{th j-tp}$ = 25 K/W.

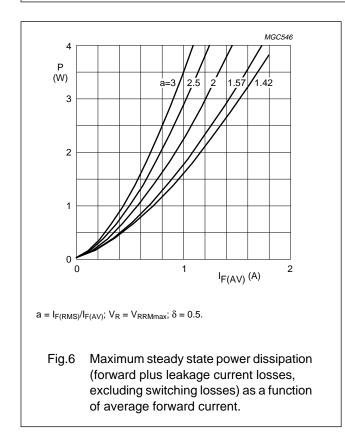
 V_{RRMmax} during 1 – δ ; curves include derating for $T_{j max}$ at V_{RRM} = 600 V.

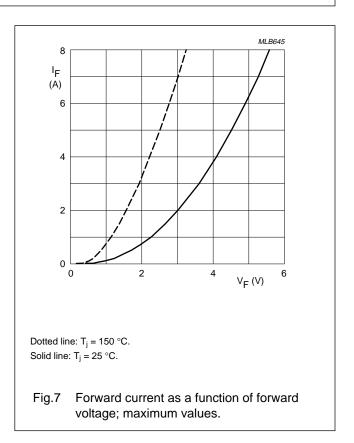
Fig.4 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

Ultra fast low-loss controlled avalanche rectifier

BYM99







Ultra fast low-loss controlled avalanche rectifier

BYM99

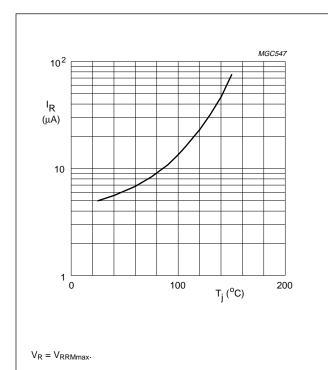


Fig.8 Reverse current as a function of junction temperature; maximum values.

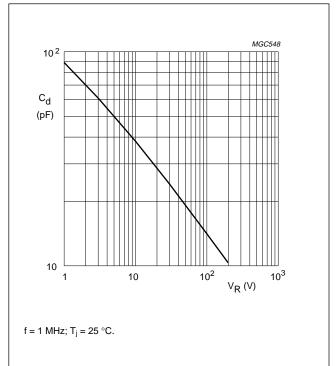
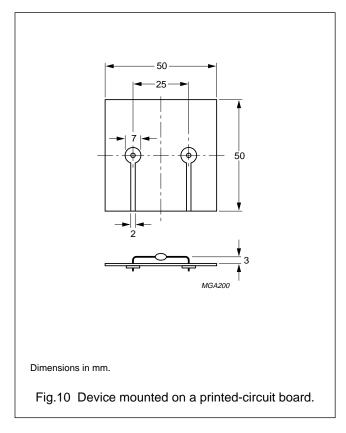
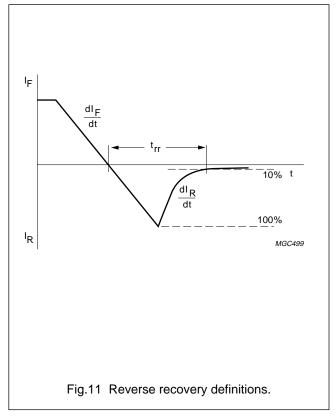


Fig.9 Diode capacitance as a function of reverse voltage; typical values.

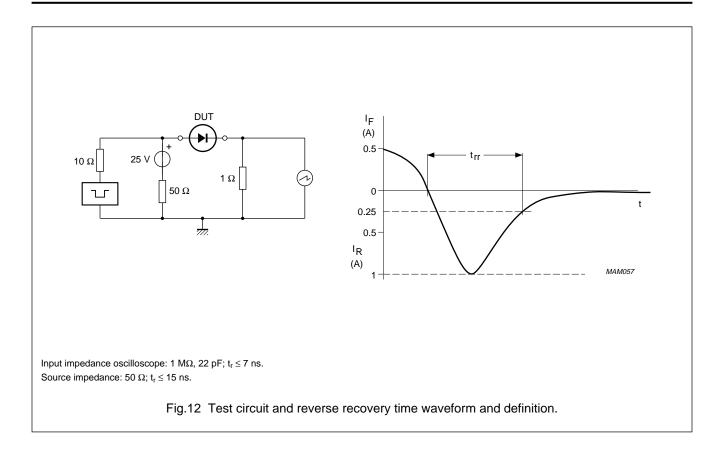




Philips Semiconductors Product specification

Ultra fast low-loss controlled avalanche rectifier

BYM99

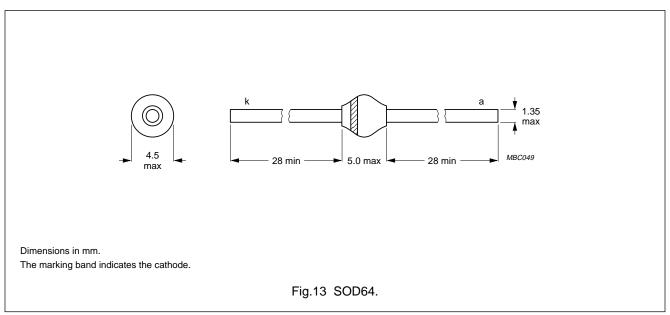


Philips Semiconductors Product specification

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PACKAGE OUTLINE



DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.

Limiting values

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.